



FINAL PRODUCT/PROCESS CHANGE NOTIFICATION #17006Generic Copy

Issue Date: 26-Feb-2013

TITLE: Final Notification for the Wafer Fab Transfer of Flip Chip Schottky Diodes (DSN2 - 0603 CSP) from ON Semiconductor ZR Fab in Phoenix (USA) to ON Semiconductor ISMF Fab in Seremban (Malaysia)

PROPOSED FIRST SHIP DATE: 3-June-2013

AFFECTED CHANGE CATEGORY(S): ON Semiconductor Fab Site

FOR ANY QUESTIONS CONCERNING THIS NOTIFICATION:

Contact your local ON Semiconductor Sales Office or Product Engineer Masitah Aznam <Masitah.Aznam @onsemi.com>

SAMPLES: Contact your local ON Semiconductor Sales Office

ADDITIONAL RELIABILITY DATA: Available

Contact your local ON Semiconductor Sales Office or Laura Rivers <laura.rivers@onsemi.com>

NOTIFICATION TYPE:

Final Product/Process Change Notification (FPCN)

Final change notification sent to customers. FPCNs are issued at least 90 days prior to implementation of the change.

ON Semiconductor will consider this change approved unless specific conditions of acceptance are provided in writing within 30 days of receipt of this notice. To do so, contact <quality@onsemi.com>.

DESCRIPTION AND PURPOSE:

ON Semiconductor is notifying customers of its plan to transfer Flip Chip Schottky Diodes (DSN2 – 0603 CSP) devices from ON Semiconductor ZR Fab in Phoenix (USA) to ON Semiconductor ISMF Fab in Seremban (Malaysia).

The ISMF facility is an ON Semiconductor owned Wafer Fab that has been producing products for ON Semiconductor since 1998. Several existing technologies within ON Semiconductor's product families are currently sourced from ISMF. ON Semiconductor Seremban Wafer Fab are TS16949, ISO-9001 and ISO-14000 certified.

Qualification tests are designed to show that the reliability of transferred devices will continue to meet or exceed ON Semiconductor standards.

**FINAL PRODUCT/PROCESS CHANGE NOTIFICATION #17006****RELIABILITY DATA SUMMARY:**

Reliability testing was performed on qualification vehicles chosen based on die size, voltage rating, and run rates.

Reliability Test Results:**NSR20F30NXT5G**

Test:	Conditions:	Interval:	Results
HTRB	Ta=150°C, 80% Rated Voltage	504 hrs	0/240
Autoclave	Ta=121°C RH=100% ~15 psig	96 hrs	0/240
HTSL	Ta = 150°C	504 hrs	0/240
H3TRB	Ta=85°C RH=85% Bias=80% rated V or 100V Max	504 hrs	0/240
IOL	Ta=25°C, Delta TJ = 100°C, Ton/off = 2 min.	7500 cycles	0/240
TC	Ta= -40°C to 125°C	500 cycles	0/240
UHASt	Ta=130C, RH=85%	96 hrs	0/240

ELECTRICAL CHARACTERISTIC SUMMARY:

Available upon request

CHANGED PART IDENTIFICATION:

Devices marked with date code June-2013 and greater will have Die from the ISMF Fab in Seremban (Malaysia).

List of affected General Parts:

NSR20F20NXT5G
NSR20F30NXT5G